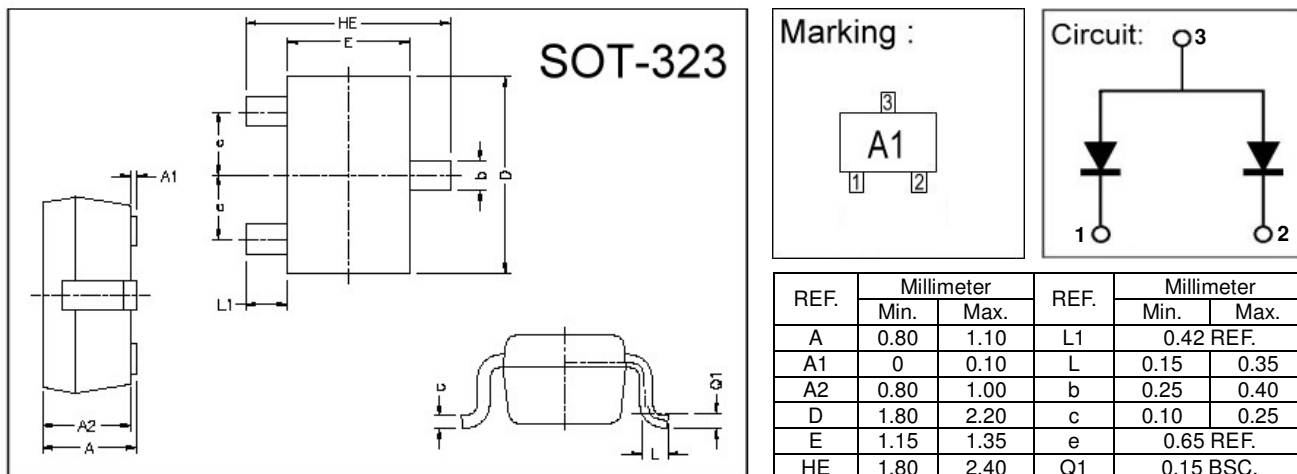


GSBAW56 SURFACE MOUNT, SWITCHING DIODE

Description

The GSBAW56 consists of two high-speed switching diodes with common anodes, fabricated in planar technology, and encapsulated in a small SOT-323 plastic SMD package.

Package Dimensions



Absolute Maximum Ratings at TA = 25°C

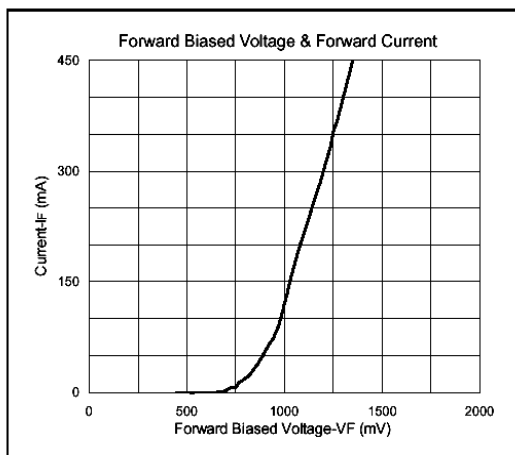
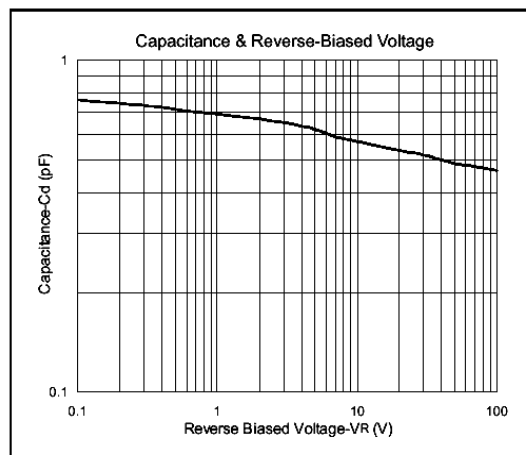
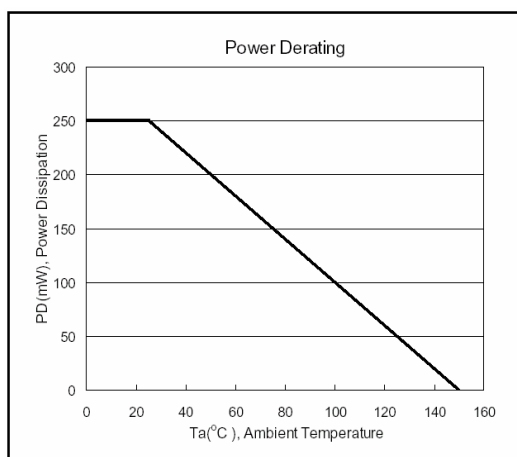
Parameter		Symbol	Ratings	Unit
Junction Temperature		Tj	+125	°C
Storage Temperature		Tstg	-65 ~ +150	°C
Repetitive Peak Reverse Voltage		VRRM	85	V
Continuous Reverse Voltage		VR	75	V
Continuous Forward Current	single diode loaded (note1)	IF	150	mA
	double diode loaded (note1)		130	
Repetitive Peak Forward Current		IFRM	500	mA
Non-Repetitive Peak Forward Current (1ms)		IFSM	1	A
Total Power Dissipation		PD	250	mW

Notes: 1. Device mounted on an FR4 printed-circuit board.

Electrical Characteristics (at TA = 25°C unless otherwise noted)

Parameter	Symbol	Min.	Max.	Unit	Test Conditions
Reverse Voltage	VR	85	-	V	IR=100uA
Forward Voltage	VF(1)	-	715	mV	IF=1mA
	VF(2)	-	855	mV	IF=10mA
	VF(3)	-	1000	mV	IF=50mA
	VF(4)	-	1250	mV	IF=150mA
Reverse Current	IR	-	1	uA	VR=80V
Diode Capacitance	CD		2	pF	VR=0, f=1MHz
Reverse Recovery Time	Trr	-	4	nS	IF=IR=10mA, RL=100Ω measured at IR=1mA

Characteristics Curve

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